





S4D10120A/S4D10120E/S4D10120H/S4D10120F 1200V SIC POWER SCHOTTKY RECTIFIERS

Description

This 1200V 10A diode is high voltage Schottky rectifier that has very low total conduction losses and very stable switching characteristics over temperature extremes. The

S4D10120A/S4D10120E/S4D10120H/S4D10120F are ideal for energy sensitive, high frequency applications in challenging environments.

Features

- 175°C T_J operation
- Ultra-low switching loss
- · Switching speeds independent of operating temperature
- Low total conduction losses
- · High forward surge current capability
- High package isolation voltage
- Terminals finish: 100% Pure Tin
- "-A" is an AEC-Q101 qualified device
- Pb Free Device
- All SMC parts are traceable to the wafer lot
- Additional electrical and life testing can be performed upon request

Applications

- Alternative energy inverters
- Power Factor Correction (PFC)
- Free-Wheeling diodes
- · Switching supply output rectification
- · Reverse polarity protection

S4D10120A	S4D10120E	S4D10120F	S4D10120H
1 2 K	K 2	1 2 K	1 2
TO-220AC	DPAK	ITO-220AC	TO-247AC
(TO-220-2)	(TO-252-2)	(TO-220-F2)	(TO-247-2)
PIN 1 O—PIN 2 O—	1. Cathode 2. Anode		







Maximum Ratings:

Characteristics	Symbol	Condition	Max.	Units
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	$egin{array}{c} V_{RRM} \ V_{R} \end{array}$	-	1200	V
Average Rectified Forward Current	I _{F (AV)1}	Tc =25°C	33	Α
	I _{F (AV)2}	Tc =153°C	10	Α
	I_{FRM1}	10 ms, Half Sine pulse , Tc =25°C	46	Α
Repetitive Peak Forward Surge Current	I _{FRM2}	10 ms, Half Sine pulse , Tc =110°C	30	Α
	I _{FSM1}	10ms, Half Sine pulse, Tc =25°C	105	Α
Peak One Cycle Non-Repetitive Surge Current	I _{FSM2}	10ms, Half Sine pulse, Tc =110°C	80	А
	I _{F,Max1}	10μs. Pulse, Tc=25°C	750	Α
Non-Repetitive Peak Forward Surge Current	I _{F,Max2}	10µs. Pulse, Tc=110℃	620	А
	P _{tot1}	Tc =25°C	150.0	W
Power Dissipation	P _{tot2}	Tc=110°C	65.0	W

Electrical Characteristics:

Characteristics	Symbol	Condition	Тур.	Max.	Units
Forward Voltage Drop*	V _{F1}	@ 10A, Pulse, T _J = 25 °C	1.5	1.8	V
	V _{F2}	@ 10A, Pulse, T _J = 175 °C	2.2	3.0	V
Reverse Current*	I _{R1}	@V _R = rated V _R T _J = 25 °C	2	30	uA
	I _{R2}	$@V_R = \text{rated } V_R$ $T_J = 175 ^{\circ}\text{C}$	8	40	uA
Junction Capacitance	C _T	V _R =0V, T _J =25°C, f=1MHz	772	-	pF
Reverse Recovery Charge	Qc	I _F = 10A, di/dt = 200A/µs VR = 800 V, T _J =25°C	56.46	-	nC
Capacitance Stored Energy	Ec	V _R = 800 V	30.51	-	μЈ

^{*} Pulse width < 300 μ s, duty cycle < 2

Thermal-Mechanical Specifications:

Characteristics	Symbol	S4D10120A	S4D10120E	S4D10120H	S4D10120F	Units
Junction Temperature	T_J	-55 to +175			°C	
Storage Temperature	T_{stg}	-55 to +175			°C	
Typical Thermal Resistance Junction to Case	R _{eJC}	0.9	0.9	0.98	4	°C/W

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Ratings and Characteristics Curves

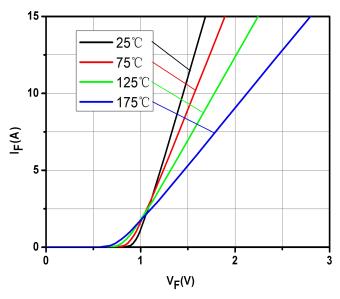


Fig.1-Typical Forward Voltage Characteristics

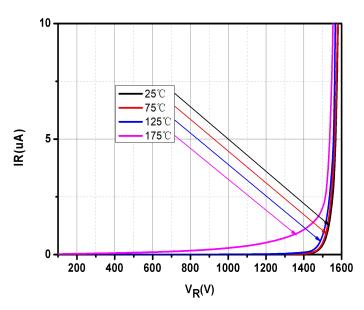


Fig.2-Typical Reverse Characteristics

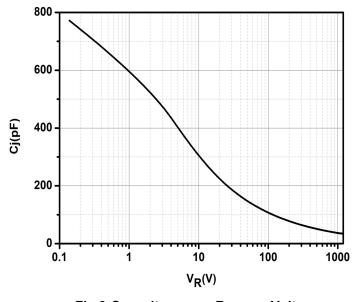


Fig.3-Capacitance vs. Reverse Voltage

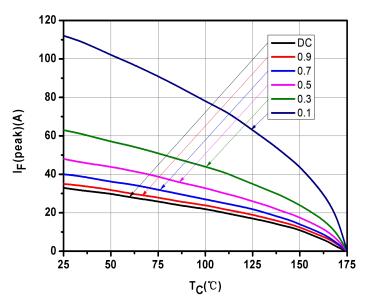


Fig.4-Current Derating







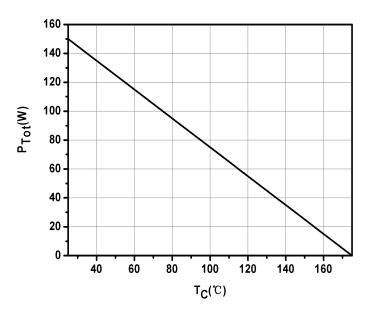


Fig.5-Power Derating

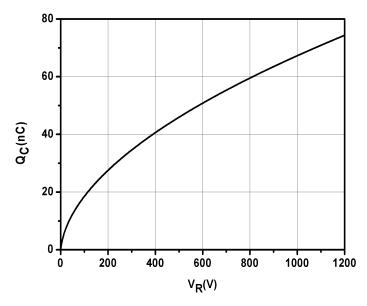


Fig.6-Total Capacitance Charge vs. Reverse Voltage

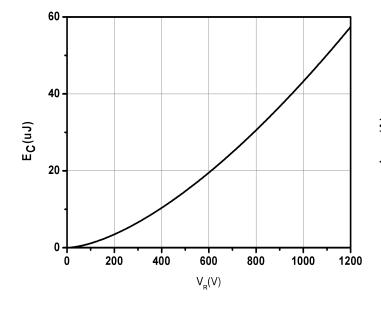


Fig.7-Capacitance Stored Energy

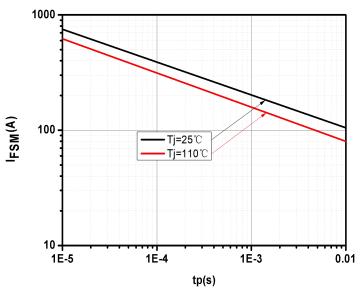


Fig.8-Non-repetitive peak forward surge current versus pulse duration (sinusoidal waveform)

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Ordering Information

Device	Package	Shipping
S4D10120A	TO-220AC(TO-220-2)	50pcs / tube
S4D10120E	DPAK(TO-252-2)	2500pcs / reel
S4D10120ETR	DPAK(TO-252-2)	2500pcs / reel
S4D10120H	TO-247AC(TO-247-2)	25pcs / tube
S4D10120F	ITO-220AC(TO-220-F2)	50pcs / tube

Marking Diagram



Where XXXXX is YYWWL

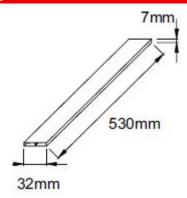
S4D = Device Type = Package type = Forward Current (10A) A/E/H/F 10 120 = Reverse Voltage (1200V) SSG = SSG = Year

= Week WW = Lot Number

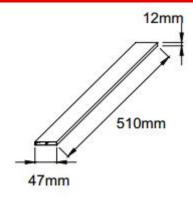
Cautions: Molding resin

Epoxy resin UL:94V-0

Tube Specification



TO-220AC(TO-220-2) ITO-220AC(TO-220-F2)



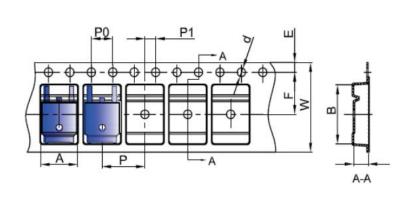
TO-247AC(TO-247-2)





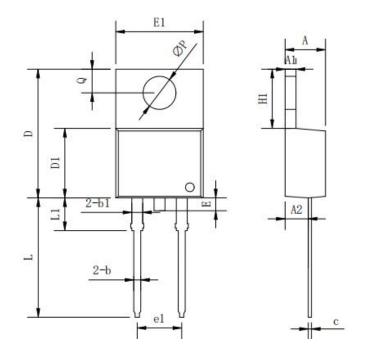


Carrier Tape & Reel Specification DPAK(TO-252-2)



SYMBOL	Millimet	ters
STWIBOL	Min.	Max.
Α	6.80	7.00
В	10.40	10.60
С	2.60	2.80
d	Ф1.45	Ф1.65
Е	1.65	1.85
F	7.40	7.60
P0	3.90	4.10
Р	7.90	8.10
P1	1.90	2.10
W	15.90	16.30

Mechanical Dimensions TO-220AC(TO-220-2)



Symbol	Dimensions in millimeters		
	Min.	Typical	Max.
Α	3.56	-	4.83
A1	0.51	-	1.40
A2	2.03	-	2.92
b	0.38	-	1.02
b1	1.14	-	1.78
С	0.31	-	0.61
D	14.22	-	16.51
D1	8.38	-	9.42
E	-	-	1.78
E1	9.65	10.16	10.67
e1	-	5.08	-
H1	5.84	-	6.86
L	12.70	-	14.73
L1	-	-	6.35
ФР	-	3.56	-

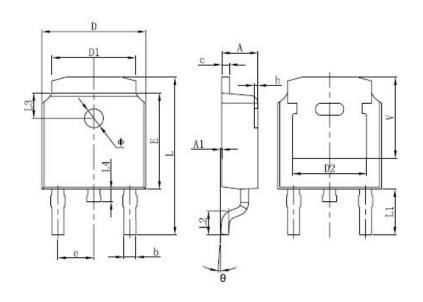
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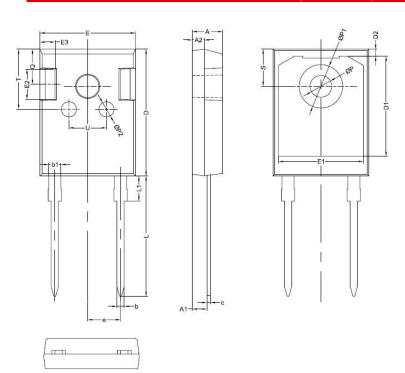


Mechanical Dimensions DPAK(TO-252-2)



SYMBOL	Dimensions in millimeters		
	Min.	Тур.	Max.
Α	2.18	-	2.39
A1	-	-	0.13
b	0.64	-	0.89
С	0.46	-	0.89
D	6.35	-	6.73
D1	4.95	-	5.46
D2	4.32	-	-
E	5.97	6.1	6.22
е	2.29BSC		
L	9.4	-	10.41
L1		2.90 REF.	
L2	1.4	1.52	1.78
L3	1.60 REF.		
L4	-	-	1.02
Ф	1.1	-	1.3
Θ	0°	-	10°
V	5.21	-	_

Mechanical Dimensions TO-247AC(TO-247-2)



CVMDOL		Millimeters	
SYMBOL	MIN.	TYP.	MAX.
Α	4.80	5.00	5.20
A1	2.20	2.41	2.61
A2	1.90	2.00	2.10
b	1.10	1.20	1.35
b1	1.80	2.00	2.20
С	0.50	0.60	0.75
D	20.30	21.00	21.20
D1		16.58	
D2		1.17	
D2 E	15.60	15.80	16.00
E1		14.02	
E2		5.00	
E3		2.50	
е		5.44	
L	19.42	19.92	20.42
L1		4.13	
P	3.50	3.60	3.70
P1	7.1	7.19	7.40
P2		2.50	
Q		5.80	
Q S	6.05	6.15	6.25
T		10.00	
U		6.20	

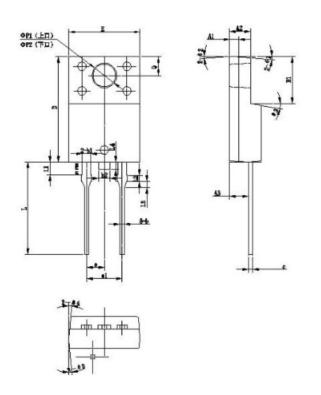
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Mechanical Dimensions ITO-220AC(TO-220-2F)



	Dimensions in millimeters			
Symbol	Min.	Max.		
Α	4.30	Typical 4.0	4.70	
A1	7.00	1.30	4.70	
A2	2.80	3.00	3.20	
A3	2.50	2.70	2.90	
b	0.5	0.6	0.75	
b1		1.20		
b2		1.60		
е	0.55	0.6	0.75	
D	14.80	15.00	15.20	
E	8.96	10.14	10.36	
е		2.55		
e1		5.10		
H1	8.50	8.70	8.90	
L	17.70	18.20	18.70	
L1		1.80		
L2		1.00		
L3		0.80		
L4		1.10		
ФР1(上口)	3.30	3.50	3.70	
ΦP1 (下口)	2.99	3.19	3.39	
Q ´	2.50	2.70	2.90	
Θ1		5°		
Θ2		4°		
Θ3		10°		
Θ4		5°		
Θ5		5°		









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